

R-C Thermal Model Parameters

DESCRIPTION

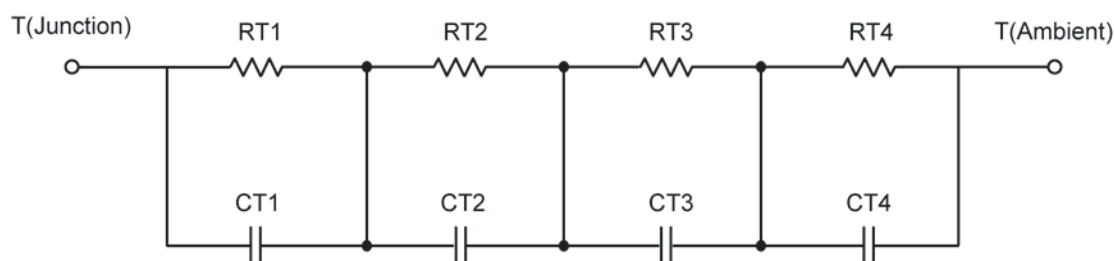
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPIICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPIICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	13.9793	N/A	31.9930
RT2	27.6092	N/A	7.1035
RT3	32.8136	N/A	26.7539
RT4	45.5979	N/A	19.1496
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	161.2130 u	N/A	2.7685 m
CT2	55.2082 m	N/A	236.5687 u
CT3	3.8601 m	N/A	18.0970 m
CT4	2.1658	N/A	1.9559 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	14.1829	N/A	11.9058
RF2	33.2644	N/A	48.5088
RF3	26.3643	N/A	21.4335
RF4	46.1884	N/A	3.1519
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	151.5771 u	N/A	219.0136 u
CF2	2.9696 m	N/A	999.4882 u
CF3	37.7652 m	N/A	12.5223 m
CF4	1.9506	N/A	651.3090 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

